Amendments to the Claims:

Listing of Claims:

Claims 1-241 (canceled)

242. (currently amended) A ~~chip packaging~~ method for fabricating a chip package comprising:

joining a die and a substrate, said die having a top surface at horizontal level, wherein said die and said substrate are under said horizontal level;

after said joining said die and said substrate, forming a patterned circuit layer over said horizontal level, said patterned circuit layer extending across an edge of said die;

after said joining said die and said substrate, forming ~~depositing~~ a passive device over said horizontal level, ~~substrate,~~ wherein said passive device is entirely ~~has a portion~~ not directly over said die; and

separating said substrate into multiple portions.

243. (currently amended) A ~~chip packaging~~ method for fabricating a chip package comprising:

joining a die and a substrate, said die having a top surface at horizontal level, wherein said die and said substrate are under said horizontal level;

after said joining said die and said substrate, forming ~~depositing~~ a passive device over said horizontal level, said passive device having a first connection point connected to said die;

after said forming ~~depositing~~ said passive device, forming ~~depositing~~ a metal bump over said horizontal level, wherein said metal bump is connected to a second connection point of said passive device; and

separating said substrate into multiple portions.

244. (currently amended) A ~~chip packaging~~ method for fabricating a chip package comprising:

providing a first die having a first top surface at a horizontal level;

providing a second die having a second top surface at said horizontal level;

forming ~~depositing~~ a passive device over said horizontal level, wherein said passive device is entirely ~~has a portion~~ not directly over said first and second dies; ~~and~~

after said forming said passive device over said horizontal level, forming an insulating layer on said passive device; and

forming ~~depositing~~ a patterned circuit layer ~~metal trace~~ over said horizontal level, wherein said patterned circuit layer ~~metal trace~~ extends across an edge of said first ~~or second~~ die.

245. (currently amended) The method of claim 242, wherein said substrate comprises a metal substrate.

246. (previously presented) The method of claim 242 further comprising joining a film and said substrate, an opening in said film exposing said substrate, followed by said joining said die and said substrate exposed by said opening.

247. (currently amended) The method of claim 246, wherein forming said opening in said film comprising a punching process.

248. (currently amended) The method of claim 246, wherein said film comprises a metal layer.

Claim 249 (canceled)

250. (currently amended) The method of claim 242, ~~249,~~ wherein said forming ~~depositing~~ said patterned circuit layer comprises an electroplating process.

251. (currently amended) The method of claim 242, ~~249,~~ wherein said forming ~~depositing~~ said patterned circuit layer comprises a sputtering process.

252. (currently amended) The method of claim 242, wherein said forming ~~depositing~~ said passive device comprises an electroplating process.

253. (withdrawn - currently amended) The method of claim 242, wherein said forming ~~depositing~~ said passive device comprises a sputtering process.

254. (currently amended) The method of claim 242, after said joining said die and said substrate, further comprising forming ~~depositing~~ a solder bump over said horizontal level, ~~substrate,~~ followed by said separating said substrate.

255. (withdrawn - currently amended) The method of claim 242, after said joining said die and said substrate, further comprising forming ~~depositing~~ a gold bump over said horizontal level, ~~substrate,~~ followed by said separating said substrate.

256. (currently amended) The method of claim 242, wherein said forming said patterned circuit layer and said forming ~~depositing~~ said passive device are ~~is~~ followed by said separating said substrate.

257. (currently amended) The method of claim 243, wherein said substrate comprises a metal substrate.

258. (previously presented) The method of claim 243 further comprising joining a film and said substrate, an opening in said film exposing said substrate, followed by said joining said die and said substrate exposed by said opening.

259. (currently amended) The method of claim 258, wherein forming said opening in said film comprising a punching process.

260. (currently amended) The method of claim 258, wherein said film comprises a metal layer.

261. (currently amended) The method of claim 243, after said joining said die and said substrate, further comprising forming ~~depositing~~ a patterned circuit layer over said horizontal level, ~~die and over said substrate,~~ said patterned circuit layer extending across an edge of said die, followed by said separating said substrate.

262. (currently amended) The method of claim 261, wherein said forming ~~depositing~~ said patterned circuit layer comprises an electroplating process.

263. (currently amended) The method of claim 261, wherein said forming ~~depositing~~ said patterned circuit layer comprises a sputtering process.

264. (currently amended) The method of claim 243, wherein said forming ~~depositing~~ said passive device comprises an electroplating process.

265. (withdrawn - currently amended) The method of claim 243, wherein said forming ~~depositing~~ said passive device comprises a sputtering process.

266. (currently amended) The method of claim 243, wherein said forming ~~depositing~~ said metal bump comprises forming ~~depositing~~ a solder bump over said horizontal level, wherein said solder bump is connected to said second connection point.

267. (withdrawn - currently amended) The method of claim 243, wherein said forming ~~depositing~~ said metal bump comprises forming ~~depositing~~ a gold bump over said horizontal level, wherein said gold bump is connected to said second connection point.

268. (currently amended) The method of claim 243, wherein said forming ~~depositing~~ said metal bump is followed by said separating said substrate.

269. (currently amended) The method of claim 244, wherein said forming ~~depositing~~ said patterned circuit layer ~~metal trace~~ comprises an electroplating process.

270. (currently amended) The method of claim 244, wherein said forming ~~depositing~~ said patterned circuit layer ~~metal trace~~ comprises a sputtering process.

271. (currently amended) The method of claim 244, wherein said forming ~~depositing~~ said passive device comprises an electroplating process.

272. (withdrawn - currently amended) The method of claim 244, wherein said forming ~~depositing~~ said passive device comprises a sputtering process.

273. (currently amended) The method of claim 244, after said forming ~~depositing~~ said insulating layer ~~passive device~~ and said forming ~~depositing~~ said patterned circuit layer, ~~metal trace,~~ further comprising forming ~~depositing~~ a solder bump over said horizontal level.

274. (withdrawn - currently amended) The method of claim 244, after said forming ~~depositing~~ said insulating layer ~~passive device~~ and said forming ~~depositing~~ said patterned circuit layer, ~~metal trace,~~ further comprising forming ~~depositing~~ a gold bump over said horizontal level.